

## Power MOSFET

## ■ GENERAL DESCRIPTION

The XP134A11A1SR is a P-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics

Two FET devices are built into the one package.

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

The small SOP-8 package makes high density mounting possible.

## ■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

## ■ FEATURES

**Low On-State Resistance** :Rds(on)=0.065  $\Omega$  (Vgs=-10V)  
:Rds(on)=0.11  $\Omega$  (Vgs=-4.5V)

**Ultra High-Speed Switching**

**Driving Voltage** : -4.5V

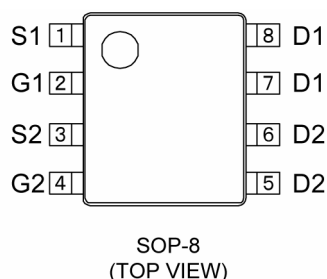
**P-Channel Power MOSFET**

**DMOS Structure**

**Two FET Devices Built-in**

**Package** : SOP-8

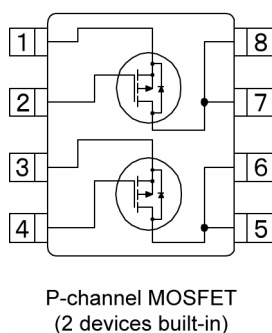
## ■ PIN CONFIGURATION



## ■ PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1	S1	Source
2	G1	Gate
3	S2	Source
4	G2	Gate
5~6	D2	Drain
7~8	D1	Drain

## ■ EQUIVALENT CIRCUIT



## ■ ABSOLUTE MAXIMUM RATINGS

Ta = 25°C

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	-30	V
Gate-Source Voltage	Vgss	±20	V
Drain Current (DC)	Id	-4	A
Drain Current (Pulse)	Idp	-16	A
Reverse Drain Current	Idr	-4	A
Channel Power Dissipation *	Pd	2	W
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55~150	°C

\* When implemented on a glass epoxy PCB

## ELECTRICAL CHARACTERISTICS

### DC Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	I <sub>dss</sub>	V <sub>ds</sub> =-30V, V <sub>gs</sub> =0V	-	-	-10	μA
Gate-Source Leak Current	I <sub>gss</sub>	V <sub>gs</sub> =±20V, V <sub>ds</sub> =0V	-	-	±1	μA
Gate-Source Cut-Off Voltage	V <sub>gs(off)</sub>	I <sub>d</sub> =-1mA, V <sub>ds</sub> =-10V	-1.0	-	-2.5	V
Drain-Source On-State Resistance *	R <sub>ds(on)</sub>	I <sub>d</sub> =-2A, V <sub>gs</sub> =-10V	-	0.055	0.065	Ω
		I <sub>d</sub> =-2A, V <sub>gs</sub> =-4.5V	-	0.09	0.11	Ω
Forward Transfer Admittance *	Y <sub>fs</sub>	I <sub>d</sub> =-2A, V <sub>ds</sub> =-10V	-	5	-	S
Body Drain Diode Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =-4A, V <sub>gs</sub> =0V	-	-0.85	-1.1	V

\*Effective during pulse test.

### Dynamic Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	C <sub>iss</sub>	V <sub>ds</sub> =-10V, V <sub>gs</sub> =0V f=1MHz	-	680	-	pF
Output Capacitance	C <sub>oss</sub>		-	450	-	pF
Feedback Capacitance	C <sub>rss</sub>		-	170	-	pF

### Switching Characteristics

Ta = 25°C

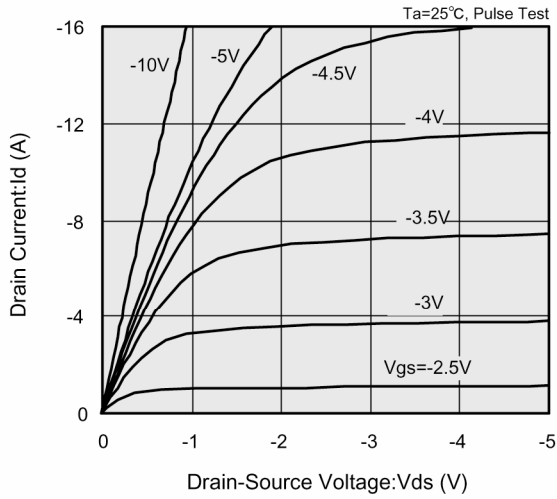
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	t <sub>d (on)</sub>	V <sub>gs</sub> =-5V, I <sub>d</sub> =-2A V <sub>dd</sub> =-10V	-	15	-	ns
Rise Time	t <sub>r</sub>		-	20	-	ns
Turn-Off Delay Time	t <sub>d (off)</sub>		-	30	-	ns
Fall Time	t <sub>f</sub>		-	20	-	ns

### Thermal Characteristics

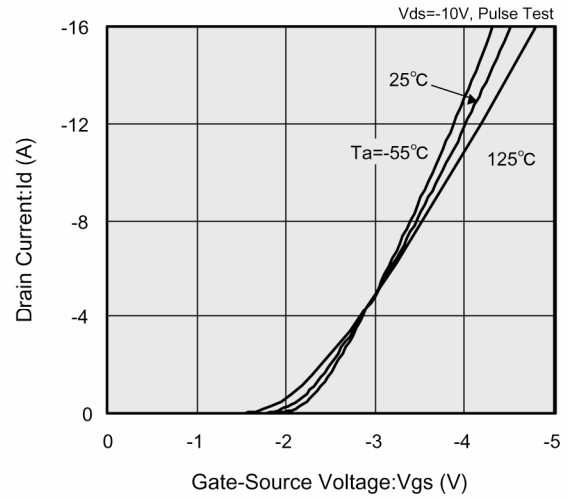
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	R <sub>th (ch-a)</sub>	Implement on a glass epoxy resin PCB	-	62.5	-	°C/W

## TYPICAL PERFORMANCE CHARACTERISTICS

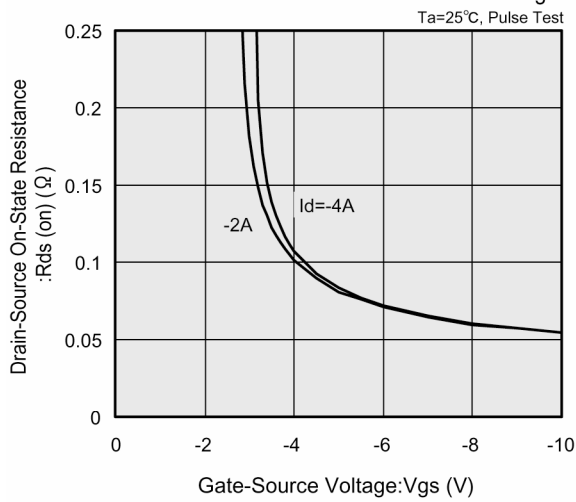
(1) Drain Current vs. Drain-Source Voltage



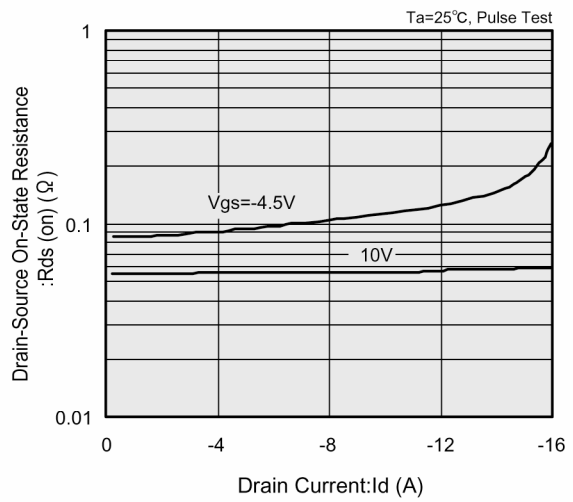
(2) Drain Current vs. Gate-Source Voltage



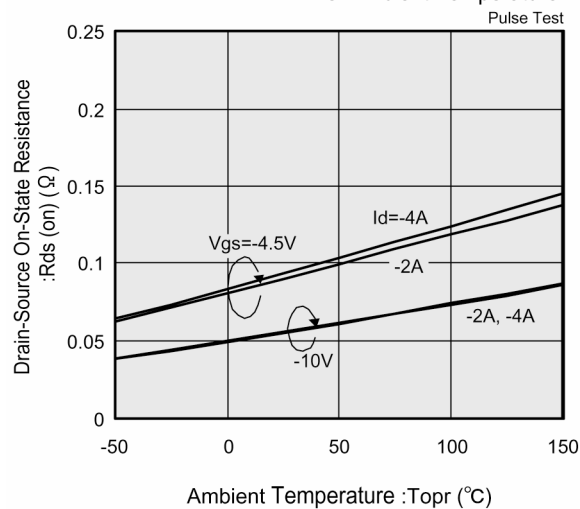
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



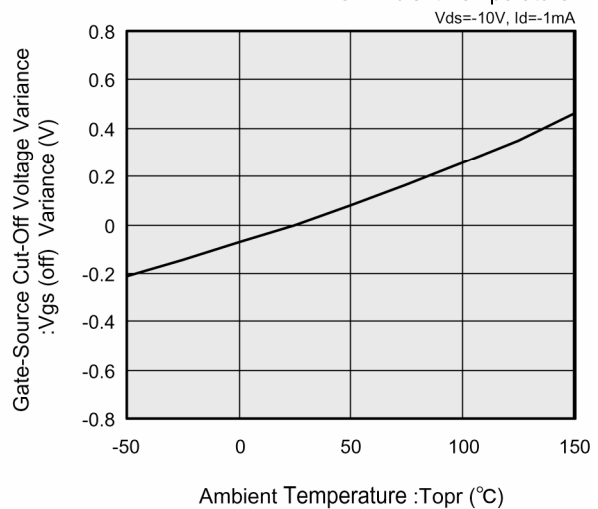
(4) Drain-Source On-State Resistance vs. Drain Current



(5) Drain-Source On-State Resistance vs. Ambient Temperature

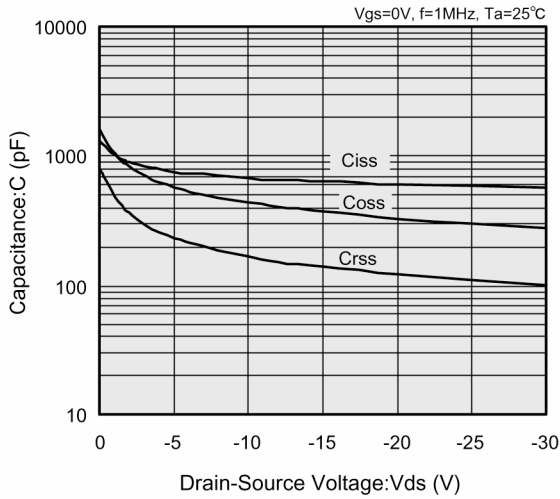


(6) Gate-Source Cut-Off Voltage Variance vs. Ambient Temperature

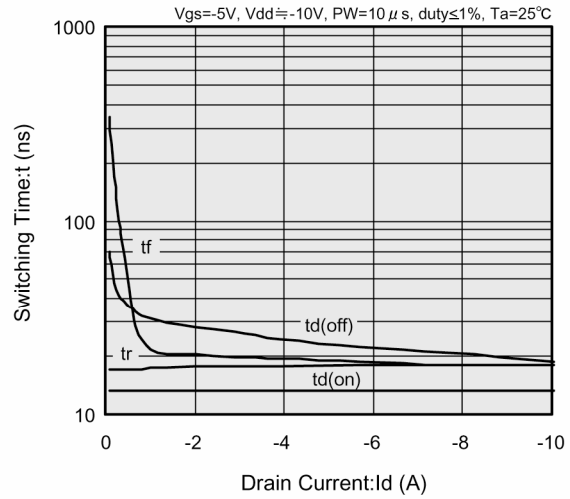


## TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

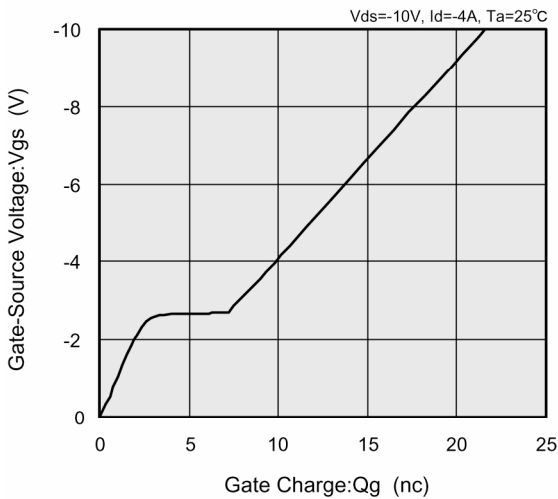
(7) Capacitance vs. Drain-Source Voltage



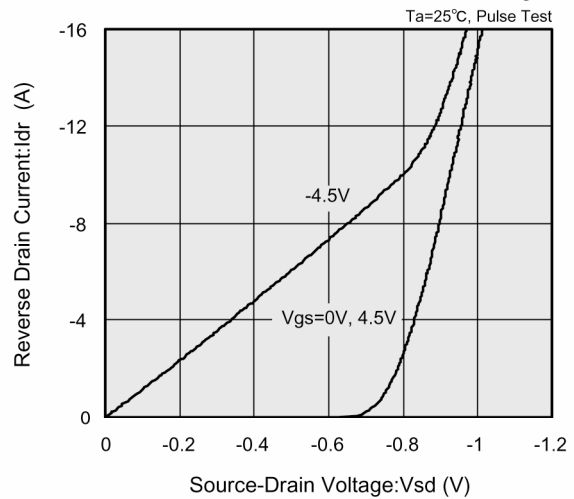
(8) Switching Time vs. Drain Current



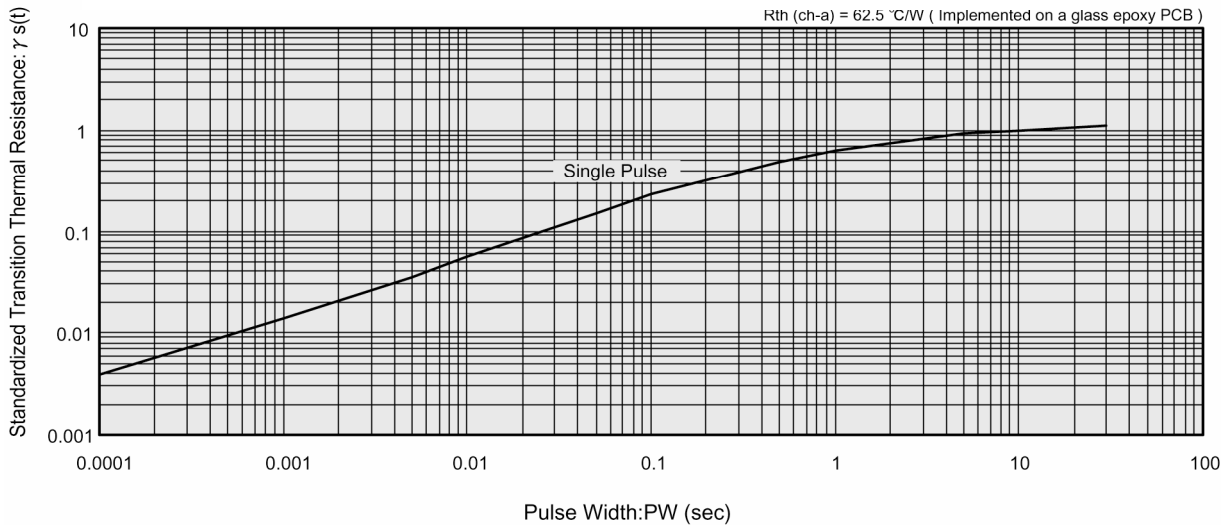
(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current vs. Source-Drain Voltage



(11) Standardized transition Thermal Resistance vs. Pulse Width



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